

Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit |
|------------------------------|------------------|-------|------|
| Collector-Base Voltage | V _{CBO} | 50 | V |
| Collector-Emitter Voltage | V _{CEO} | 45 | V |
| Emitter-Base Voltage | V _{EBO} | 6.0 | V |
| Collector Current | Ic | 100 | mA |
| Peak Pulse Collector Current | ICM | 200 | mA |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | Symbol | Value | Unit | |
|---|----------|-----------------------------------|-------------|------|--|
| Dower Dissipation | (Note 5) | D | 400 | mW | |
| Power Dissipation | (Note 6) | PD PD | 1,000 | | |
| Thermal Resistance, Junction to Ambient | (Note 5) | R ₀ JA | 310 | 0000 | |
| | (Note 6) | | 120 | °C/W | |
| Thermal Resistance, Junction to Lead | (Note 7) | R _{θJL} | 120 | °C/W | |
| Operating and Storage and Temperature Range | | T _J , T _{STG} | -55 to +150 | °C | |

ESD Ratings (Note 8)

| Characteristic | Symbol | Value | Unit | JEDEC Class |
|--|---------|-------|------|-------------|
| Electrostatic Discharge - Human Body Model | ESD HBM | 4,000 | V | 3A |
| Electrostatic Discharge - Machine Model | ESD MM | 200 | V | В |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
|---|----------------------|----------|------------|------------|----------|---|
| Collector-Base Breakdown Voltage | BV _{CBO} | 50 | — | — | V | $I_{\rm C} = 100 \mu A, I_{\rm B} = 0$ |
| Collector-Emitter Breakdown Voltage (Note 9) | BV _{CEO} | 45 | _ | _ | V | $I_{\rm C} = 10 {\rm mA}, I_{\rm B} = 0$ |
| Emitter-Base Breakdown Voltage | BVEBO | 6 | — | — | V | $I_E = 100 \mu A, I_C = 0$ |
| DC Current Gain | h _{FE} | 200 | 350 | 450 | _ | $V_{CE} = 5.0V, I_{C} = 2.0mA$ |
| Collector-Emitter Saturation Voltage (Note 9) | V _{CE(sat)} | _ | 80 200 | 250 600 | mV | $\begin{split} I_C &= 10 \text{mA}, \ I_B = 0.5 \text{mA} \\ I_C &= 100 \text{mA}, \ I_B = 5.0 \text{mA} \end{split}$ |
| Base-Emitter Saturation Voltage (Note 9) | V _{BE(sat)} | | 700 900 | — | mV | $I_{C} = 10mA, I_{B} = 0.5mA$ $I_{C} = 100mA, I_{B} = 5.0mA$ |
| Base-Emitter Voltage (Note 9) | V _{BE(ON)} | 580 — | 640 725 | 700 770 | mV | $V_{CE} = 5.0V, I_C = 2.0mA$ $V_{CE} = 5.0V, I_C = 10mA$ |
| Collector-Cutoff Current | I _{CBO} | | — | 15 5.0 | nA μA | V _{CB} = 30V V _{CB} = 30V, T _A = +150°C |
| Gain Bandwidth Product | f⊤ | 100 | _ | _ | MHz | $V_{CE} = 5.0V, I_C = 10mA, f = 100MHz$ |
| Collector-Base Capacitance | Ссво | _ | 3.0 | | pF | $V_{CB} = 10V, f = 1.0MHz$ |

5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
6. Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.
7. Thermal resistance from junction to solder-point (on the exposed collector pad).
8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.
9. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%. Notes:



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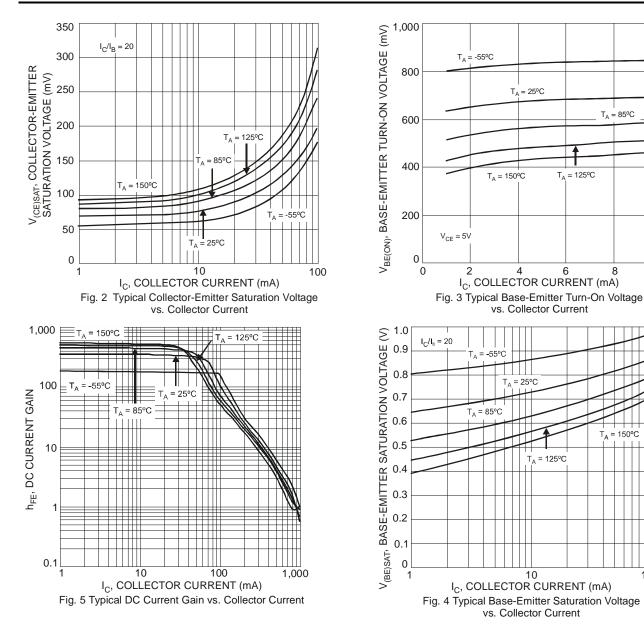
= 150°C Τ_Α

100

 $T_A = 85^{\circ}C$

T_A = 125°C

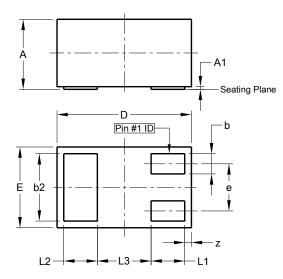
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

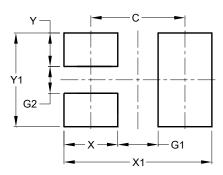
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



| X1-DFN1006-3 | | | | |
|----------------------|------|-------|------|--|
| Dim | Min | Max | Тур | |
| Α | 0.47 | 0.53 | 0.50 | |
| A1 | 0.00 | 0.05 | 0.03 | |
| b | 0.10 | 0.20 | 0.15 | |
| b2 | 0.45 | 0.55 | 0.50 | |
| D | 0.95 | 1.075 | 1.00 | |
| Е | 0.55 | 0.675 | 0.60 | |
| е | - | - | 0.35 | |
| L1 | 0.20 | 0.30 | 0.25 | |
| L2 | 0.20 | 0.30 | 0.25 | |
| L3 | - | - | 0.40 | |
| z | 0.02 | 0.08 | 0.05 | |
| All Dimensions in mm | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| С | 0.70 |
| G1 | 0.30 |
| G2 | 0.20 |
| Х | 0.40 |
| X1 | 1.10 |
| Ŷ | 0.25 |
| Y1 | 0.70 |



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